ALTERNATIVE TO PTO/SB/08a/b (06-03)

Substitute for form 1449/PTO	**Complete if Known**	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT *(Use as many sheets as necessary)*	Application Number	10/537,804
	Filing Date	June 7, 2005
	First Named Inventor	Robert DWILINSKI
	Art Unit	~~Not yet assigned~~ 1792
	Examiner Name	~~Not yet assigned~~ /Felisa Hiteshew/
Sheet 1 of 1	Attorney Docket Number	204552035400

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number — Number-Kind Code[2] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1.	5,306,662	4-26-1994	Nakamura et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document — Country Code[3]-Number[4]-Kind Code[5] *(if known)*	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
	2.	JP-5-183189	7-23-1993		abstract, also corresponds to U.S. Patent No. 5,306,662	

*EXAMINER: Initial if information considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. [1] Applicant's unique citation designation number (optional). [2] See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. [3] Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4] For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5] Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6] Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
	3.	M. K. Kelly et al. (1996) "Optical Patterning of GaN Films," Appl Phys. Lett 69(12), pp. 1749-1751	
	4.	W. S. Wong et al. (1999) "Fabrication of Thin-Film InGaN Light-Emitting Diode Membranes By Laser Lift-Off," Applied Physics Letters 75(10), pp. 1360-1362	
	5.	S. Porowski et al. (1993) "Prospects for High-Pressure Crystal Growth of III-V Nitrides," Inst. Phys. Conf. Ser. No. 137, Chapter 4, pp. 369-372	

*EXAMINER: Initial if information considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1] Applicant's unique citation designation number (optional). [2] Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	/Felisa Hiteshew/	Date Considered	04/18/2008

va-138016 ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /F.H./